

Serial No. 09/735,005  
Docket No. NEC 444  
Amendment G under Rule 116

**AMENDMENTS TO THE SPECIFICATION:**

Please amend the paragraph beginning at page 7, line 34, as follows:

Next, referring to Fig. 8C, trenches 5 are perforated in the silicon substrate 1 by etching the silicon substrate 1 using the silicon nitride layer 3 and the silicon oxide layer 2 as a mask.

This results in grid shaped trenches being formed in the element isolation region.

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